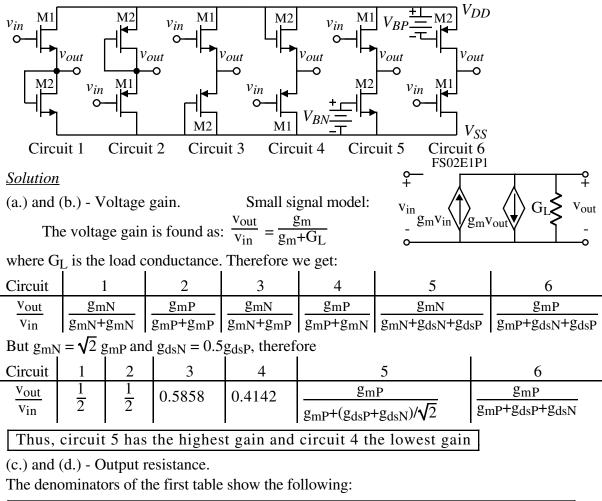
EXAMINATION NO. 1- SOLUTIONS (Average = 60, High = 88, Low = 46)

Problem 1 - (25 points)

Six versions of a source follower are shown below. Assume that $K'_N = 2K'_P$, $\lambda_P = 2\lambda_N$, all W/L ratios of all devices are equal, and that all bias currents in each device are equal. Neglect bulk effects in this problem and assume no external load resistor. Identify which circuit or circuits have the following characteristics: (a.) highest small-signal voltage gain, (b.) lowest small-signal voltage gain, (c.) the highest output resistance, (d.) the lowest output resistance, (e.) the highest $v_{out}(\max)$ and (f.) the lowest $v_{out}(\max)$.



Ckt.6 has the highest output resistance and Ckt. 1 the lowest output resistance.

(e.) Assuming no current has to be provided by the output, circuits 2, 4, and 6 can pull the output to V_{DD} . \therefore Circuits 2, 4 and 6 have the highest output swing.

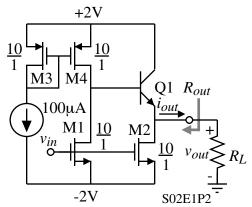
(f.) Assuming no current has to be provided by the output, circuits 1, 3, and 5 can pull the output to ground. ∴ Circuits 1, 3 and 5 have lowest output swing.

Summary Summary

- (a.) Ckt. 5 has the highest voltage gain
- (d.) Ckt. 1 has the lowest output resistance
- (b.) Ckt. 4 has the lowest voltage gain
- (e.) Ckts. 2,4 and 6 have the highest output (f.) Ckts. 1.3 and 5 have the lowest output
- (c.) Ckt. 6 has the highest output resistance (f.) Ckts. 1,3 and 5 have the lowest output

Problem 2 - (25 points)

An output stage using both MOSFETs and a BJT is shown. Assume the transistor parameters are K_N' = 110µA/V², $V_T = 0.7$ V, and $\lambda_N = 0.04$ V⁻¹ for the $\frac{10}{1}$ NMOS; $K_P' = 50$ µA/V², $V_T = -0.7$ V, and $\lambda_P =$ 0.05V⁻¹ for the PMOS and $\beta_F = 100$, $V_t = 0.025$ V, and $I_s = 10$ fA for the NPN BJT. (a.) If v_{in} can vary between ±2V, what is the maximum positive and negative value of i_{out} when $R_L = 0\Omega$? (b.) If v_{in} can vary between ±2V, what is the maximum and minimum output voltage when $R_L = 100\Omega$?



<u>Solution</u>

. .

(a.) The maximum i_{out} occurs when $v_{in} = -2V$. All of the 100µA through M4 is base current giving a maximum $i_{out} = (1+\beta)100\mu A = 10.1 \text{mA} \rightarrow i_{out}(\text{max}) = \underline{10.1 \text{mA}}$

The maximum $-i_{out}$ occurs when $v_{in} = +3V$. Since $V_{DS} = 2V$ and $V_{GS} - V_T = 3.3V$, M2 is in the triode region. Under these conditions, we assume M1 absorbs all of the 100µA of M4 and therefore the BJT is off and maximum $-i_{out}$ is,

$$-i_{out}(\max) = \frac{K_N'W}{L} [(V_{GS2} - V_T)v_{DS} - 0.5v_{DS}^2] = 110 \cdot 10[3.3 \cdot 2 - 0.5(2)^2] = 5.06 \text{mA}$$
$$-i_{out}(\max) = -5.06 \text{mA}$$

(b.) There are 2 possible answers for the maximum v_{out} . The current limited max. v_{out} is

Max.
$$v_{out} = i_{out}(\max)R_L = 10.1 \text{mA} \cdot 0.1 \text{k}\Omega = 1.01 \text{V}$$

The voltage limited $v_{out}(\max)$ is,

Max.
$$v_{out} = 2V - V_{SD4}(\text{sat}) - V_{BE1}(10.1\text{mA}) = 2 - \sqrt{\frac{2 \cdot 100}{50 \cdot 10}} - 0.025 \ln(\frac{10\text{mA}}{10\text{fA}})$$

= 2-0.6325-0.6908 = 0.6768V \therefore Max. $v_{out} = 0.6768V$

For the maximum – v_{out} we see that the $V_{GS2} = 4V$ which strongly suggests that M2 will be in the triode region. Equating the current in the 100 Ω resistor with that in M2 gives,

$$\frac{2 \cdot v_{DS}}{100} = \frac{K_N'W}{L} [(V_{GS2} \cdot V_T)v_{DS} - 0.5v_{DS}^2]$$

$$0.02 - 0.01v_{DS} = 1.1 \times 10^{-3} [3.3v_{DS} - 0.5v_{DS}^2] \rightarrow v_{DS}^2 - 24.782v_{DS} + 36.36 = 0$$

$$v_{DS} = 1.1 \times 10^{-3} [3.3v_{DS} - 0.5v_{DS}^2] \rightarrow v_{DS}^2 - 24.782v_{DS} + 36.36 = 0$$

:.
$$v_{DS} = +12.391 \pm 10.8247 \implies v_{DS} = 1.5662 \text{V}$$

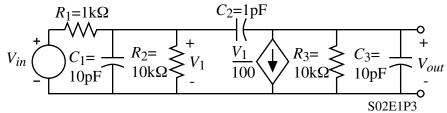
:. Max.
$$-v_{out} = -2V + 1.5662V = -0.4338V$$

The current through M2 under this condition is $\frac{110 \cdot 10}{2 \cdot 1} (1.5662 \text{V})^2 = 1.349 \text{mA}$

It can be shown that if M2 remains saturated that Max. $-v_{out} = I \cdot 100\Omega = -0.1815V$ So our assumption that M2 was in the triode region is valid.

Problem 3 - (25 points)

Find the midband voltage gain and the –3dB frequency in Hertz for the circuit shown.



<u>Solution</u>

The midband gain is given as,

$$\frac{V_{out}}{V_{in}} = -\left(\frac{10k\Omega}{100}\right) \left(\frac{10k\Omega}{11k\Omega}\right) = \underline{-90.91V/V}$$

To find the –3dB frequency requires finding the 3 open-circuit time constants.

*R*_{*C*10}:

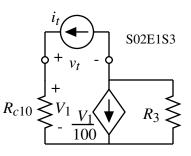
$$R_{C10} = 1\mathrm{k}\Omega || 10\mathrm{k}\Omega = 0.9091\mathrm{k}\Omega$$

$$R_{C10}C_1 = 0.9091 \cdot 10$$
ns = 9.09ns

 R_{C20} :

$$v_t = i_t R_{C10} + R_3(i_t + 0.01V_1)$$

= $i_t(R_{C10} + R_3 + 0.01R_{C10}R_3)$
∴ $R_{C20} = R_{C10} + R_3 + 0.01R_{C10}R_3$
= $0.9091 + 10(1 + 0.01 \cdot 909.1)$ kΩ = 101.82 kΩ
 $R_{C20}C_2 = 101.82 \cdot 1$ ns = 101.82 ns



*R*_{C30}:

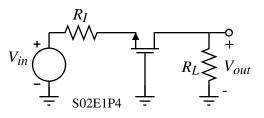
$$R_{C30} = 10 \mathrm{k}\Omega \longrightarrow R_{C30}C_3 = 10.10\mathrm{ns} = 100\mathrm{ns}$$

 $\Sigma T_0 = (9.091 + 101.82 + 100)\mathrm{ns} = 210.91\mathrm{ns} \longrightarrow \omega_{-3\mathrm{dB}} = \frac{1}{\Sigma T_0} = 4.74 \mathrm{x} 10^6 \mathrm{rad/s}$

$$f_{-3\mathrm{dB}} = \frac{4.74 \mathrm{x} 10^6}{2\pi} = \underline{754.6\mathrm{kHz}}$$

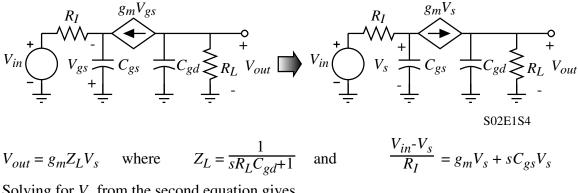
Problem 4 - (25 points)

Find the midband voltage gain and the exact value of the two poles of the voltage transfer function for the circuit shown. Assume that $R_I = 1k\Omega$, $R_L = 10K\Omega$, $g_m = 1mS$, $C_{gs} = 5pF$ and $C_{gd} = 1$ pF. Ignore r_{ds} .



<u>Solution</u>

The best approach to this problem is a direct analysis. Small-signal model:



Solving for V_s from the second equation gives,

$$V_s = \frac{V_{in}}{1 + g_m R_I + s C_{gs} R_I}$$

Substituting V_s in the first equation gives,

$$V_{out} = g_m Z_L \frac{V_{in}}{1 + g_m R_I + sC_{gs} R_I} \rightarrow \frac{V_{out}}{V_{in}} = g_m \left(\frac{1}{sR_L C_{gd} + 1}\right) \left(\frac{1}{1 + g_m R_I + sC_{gs} R_I}\right)$$
$$= \left(\frac{g_m R_L}{1 + g_m R_I}\right) \left(\frac{1}{sR_L C_{gd} + 1}\right) \left(\frac{1}{\frac{sC_{gd} R_I}{1 + g_m R_I} + 1}\right) = \text{MBG}\left(\frac{1}{1 - \frac{s}{p_1}}\right) \left(\frac{1}{1 - \frac{s}{p_2}}\right)$$
$$\therefore \text{ MBG} = \left(\frac{g_m R_L}{1 + g_m R_I}\right) = \left(\frac{1 \cdot 10}{1 + 1 \cdot 1}\right) = \underbrace{5V/V}_{I}$$
$$p_1 = -\frac{1}{R_L C_{gd}} = -\frac{1}{10 \cdot 1 \text{ ns}} = \underbrace{-10^8 \text{ rad/s}}_{I} \text{ and } p_2 = -\frac{1 + g_m R_I}{R_I C_{gs}} = -\frac{1 + 1}{1 \cdot 5 \text{ ns}} = \underbrace{-4x \cdot 10^8 \text{ rad/s}}_{I}$$